

**AMENDMENTS TO THE SPECIFICATION**

On page <sup>25</sup>~~26~~, please amend the paragraph beginning at line 20 and bridging to page 27, to read as follows:

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1/9/09

[Example 1]

Fig. 1 shows a plan view and a sectional view illustrating one example of an electrode substrate and a thin film transistor of the present invention and their production methods. The lower electrode 2 and the insulating film 3 were layered sequentially in this order on the substrate 1, for example, with the same members and forming methods as in Fig. 13. However, in the present example, the pattern of a gate electrode to be the lower electrode 2 had two openings disposed adjacently to each other. In the present example, because the photosensitive lyophobic film 4 was coated by dip coating before backside exposure, the photosensitive lyophobic film 4 adhered to the surface of the insulating film 3 as well as to the back surface of the substrate 1 (Fig. 1(a)). With backside exposure, the photosensitive lyophobic film 4 was removed from the back surface of the substrate 1 to form a lyophobic region having a pattern approximately the same as that of the lower electrode 2 on the surface of the ~~insulating film 4~~ insulating film 3 (Figs. 1(b) and (c)). A conductive ink made of a liquid material containing at least one of a metal ultrafine particle material, a metal complex and a conductive polymer, was coated on two lyophilic regions surrounded by the lyophobic region, formed on the insulating film 3, and the coating ink was baked to form upper electrodes 5 and 6 (Fig. 1(d)). No particular constraint is imposed on the conductive ink, as long as the conductive ink is a liquid material having such properties that it is repelled from the lyophobic region formed of the photosensitive lyophobic film 4 and it wets and spreads over the lyophilic region from which the photosensitive lyophobic film 4 is removed, and exhibits a sufficiently low resistance value after baking; specific examples of such a material to be usable include a solution in which a metal ultrafine particle material of about 10 nm or less in